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Joint ICTP-IAEA Workshop on Physics of Radiation Effect and its Simulation for Non-Metallic Condensed Matter | (smr 2359)

Friday 17 August 2012

**Radiation induced defects in semiconductors: Optical study - Adriatico Guest House
Kastler Lecture Hall (09:00-10:30)**

Besides electronically active defects, radiation introduces defects which give rise to a level falling in the valence or conduction band, and therefore are not active. However, such radiation induced defects affect the optical properties of the semiconductor. Absorption spectroscopy may provide useful chemical and structural information, particularly when applied at cryogenic temperatures. One important advantage of photoluminescence (PL) spectroscopy is its high spectral resolution, which renders the technique sensitive to isotope or mechanical stress effects. In this talk, an overview of radiation introduced (gamma rays, electrons, protons, ions) studied by IR and PL will be given.

time	title	presenter
09:00	Radiation induced defects in semiconductors: Optical study	IVANA CAPAN